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Application Numb	er: <u>10/082,852</u>
Filing Date: 2-	25-02
First Named Inven	tor: James D. Beasom
Group Art Unit:_	2812
Examiner Name:	
Attorney Docket:	INT-0009A

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT U.S. Patent Documents Examiner Cite U.S.Patent Kind Name of Patentee or Date of Pages, Columns, Lines Where Initials Applicant of Cited Document Number Code Publication Relevant Passages or Figures Appear No. M 7-1997 5,652,153 Beasom 5-2001 6,225,181 Gregory Wong et al. 6,258,641 7-2001 5,633,180 5-1997 Bajor 5,897,362 Wallace 4-1999 Cite Office Kind Name of Patentee or Date of Location of T Examiner Number Relevant Initials Code **Publication** No. Applicant Passages/Figures MM-DD-YY Other Prior Art - Non Patent Literature Documents Name of Author (All Caps), Title of Article/Item, Date, Page(s), Volume-Issue Number(s), T Cite Examiner Initials Publisher, City and/or Country Where Published No Sze, S.M. "Semiconductor Devices, Physics and Technology" John Wiley & Sons, Pg 384 Examiner Date Considered Signature

**EXAMINER: Initial citation considered. Draw line through citation if no in conformance and not considered. Include the copy of this form with next communication to application.

112/105 5/16/02

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Signature		, A	1	M	_				Considered	03/09/	04		

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